

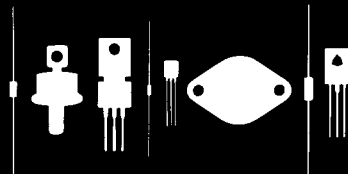
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145 Adams Avenue
Hauppauge, New York 11788



2N398
2N398A
2N398B

PNP GERMANIUM TRANSISTOR

JEDEC TO-5 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N398 Series types are PNP Germanium Transistors designed for high voltage applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL	2N398	2N398A	2N398B	UNIT
Collector-Base Voltage	V _{CB0}	105	105	105	V
Collector-Emitter Voltage	V _{CES}	105	105	105	V
Emitter-Base Voltage	V _{EBO}	50	50	75	V
Collector Current	I _C	100	200	200	mA
Emitter Current	I _E	100	200	200	mA
Power Dissipation	P _D	150	150	250	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 TO +100			°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N398		2N398A		2N398B		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} =2.5V		14		14		6.0	μA
I _{CBO}	V _{CB} =105V		-		50		25	μA
I _{CBO}	V _{CB} =105V, T _A =71°C		-		-		300	μA
I _{EBO}	V _{EB} =2.5V		-		-		6.0	μA
I _{EBO}	V _{EB} =50V		-		50		-	μA
I _{EBO}	V _{EB} =75V		-		-		50	μA
I _{CES}	V _{EB} =105V		600		600		300	μA
I _{CER}	V _{CE} =55V, R _{BE} =10kΩ		-		-		300	μA
BV _{CB0}	I _C =50μA	105		-		-		V
BV _{EBO}	I _E =50μA	50		-		-		V
V _{PT}	V _{BE} (f ₁)=1.0V, R _{BE} =11MΩ	105		105		105		V
V _{CE} (SAT)	I _C =5.0mA, I _B =0.25mA		0.35		0.35		0.25	V
V _{BE} (SAT)	I _C =5.0mA, I _B =0.25mA		0.4		0.4		0.3	V
h _{FE}	V _{CE} =0.35V, I _C =5.0mA	20		20		-		
h _{FE}	V _{CE} =0.25V, I _C =5.0mA	-		-		20		
h _{fe}	V _{CE} =6.0V, I _C =1.0mA, f=1.0kHz	-		20		40		
f _{hfb}	V _{CB} =6.0V, I _E =1.0mA, f=1.0kHz	-		-		1.0		MHz